

**IN THE CLAIMS**

Please amend the claims as follows:

1-10. (Canceled)

11. (Currently amended) An epitaxial growth method comprising:  
growing an epitaxial layer on a layered substrate which exhibits bowing so as to reduce  
said bowing, wherein the layered substrate has at least two layers, wherein at least two of  
the layers have different thermal coefficients and have the same growth temperature.

12. (Previously presented) The epitaxial growth method of claim 11 further  
comprising the step of selective etching a portion of the epitaxial layer.

13. (Original) The epitaxial growth method of claim 11 wherein the epitaxial  
layer comprises a III-V nitrides alloy and the material of the top layer of the layered  
substrate is selected from the group consisting of sapphire, silicon, silicon carbide, zinc  
oxide, gallium arsenide, gallium phosphide, indium phosphide,  $\text{LiGaO}_2$ , and  $\text{LiAlO}_2$ .

14. (Original) The epitaxial growth method of claim 11 wherein the epitaxial  
layer comprises a III-V nitrides alloy and the substrate is selected from the group  
consisting of sapphire on silicon, sapphire on a III-V nitrides alloy, sapphire on zinc  
oxide, and sapphire on silicon carbide.

15-23. (Canceled)

24. (Previously presented) The epitaxial growth method of claim 11 further  
comprising the step of removing the layered substrate after growing the epitaxial layer.

25. (Previously presented) The epitaxial growth method of claim 24 wherein the  
step of removing comprises mechanical polishing.

26. (Previously presented) The epitaxial growth method of claim 11 wherein a process of forming said layered substrate includes a heating step, wherein said layered substrate exhibits the bowing after being cooled down from said heating step.

27. (Canceled)